### NINO development

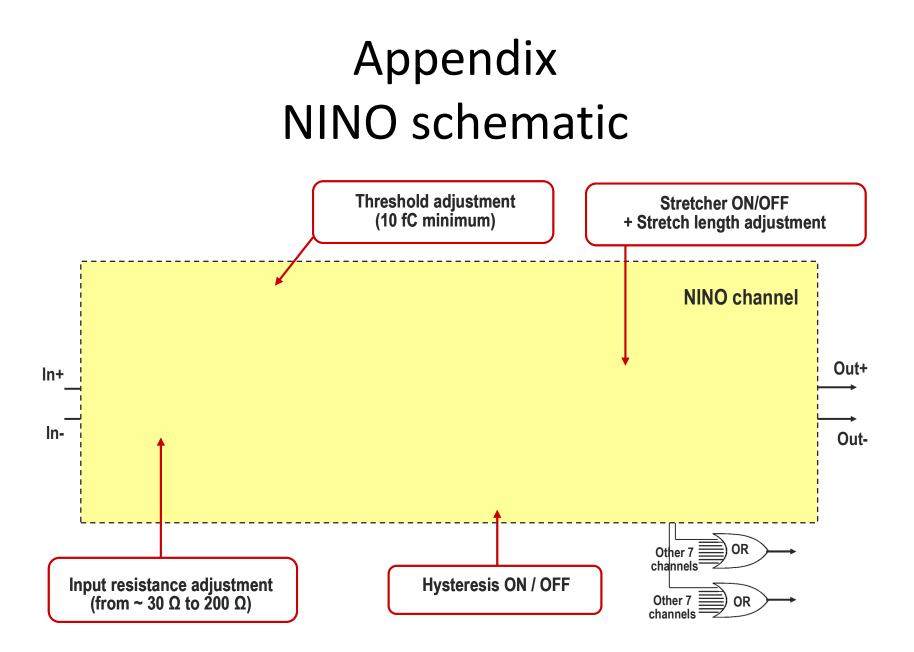
P. Jarron 14/02/2011

# Status

- NINO status
  - Used successfully connected to HPTDC in ALICE TOF
  - Jitter limit
    - 2-3 ps rms (Crispin)
  - Used for PET TOF (Endotofpet-us EU project) with 220 ps
    FWHM coincidence
    - with SiPM coupled to LSO crystal, 70 ps rms limited by Poisson statistics, so far the best results
  - a version 32 channel has been developed
  - A prototype in 130 nm has been developed

### Interest for a new development

- Arguments to continue the development of NINO
  - So far it is the best amplifier-discriminator optimized for low jitter and low threshold
    - Is ESE is interested to keep this technology alive?
  - With a new HPTDC in 130 nm (90 nm) to be developed a front end interfacing a detector is essential.
  - Why?
    - Because an integrated ASIC has many advantages
      - Simplification of the readout system, lower cost, lower power
      - It has been verified (Crispin) that the physical connection between NINO and HPTDC increases the jitter,
      - not an issue for 30 ps time resolution
      - But critical for 10 ps time resolution
- Design effort estimate
  - One year of prototype development and design
  - ½ year of characterization
  - ½ year of contingency, resubmission
  - Plus time of design for integration with HPTDC



# Time jitter limit from Crispin NINO 25

- 4 different values of injected charge and 4 different values of threshold
- Typical jitter between 2 and 3 ps With LeCroy oscilloscope
  - Input signal is 25-100 fC, for lower signal jitter dominated by electronic noise

Jitter of single channel:

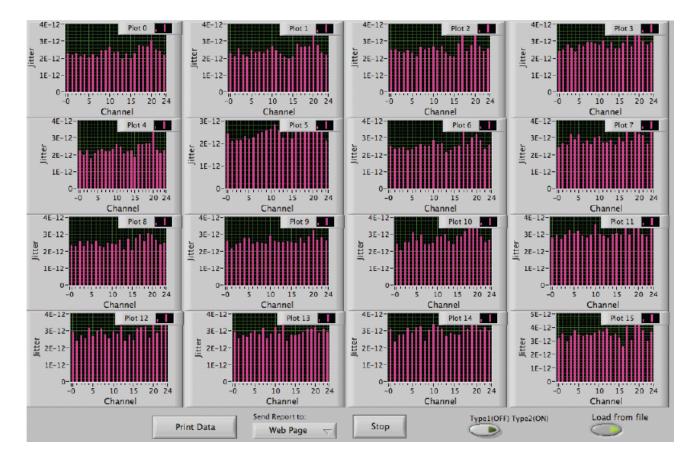
Front-end card not connected to anything

#### **7 ps**

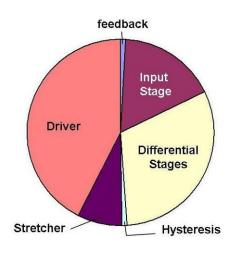
Front end card plugged into interface card

#### 14 ps

Front end cards plugged into interface card that is connected to mrpc strip 21 ps

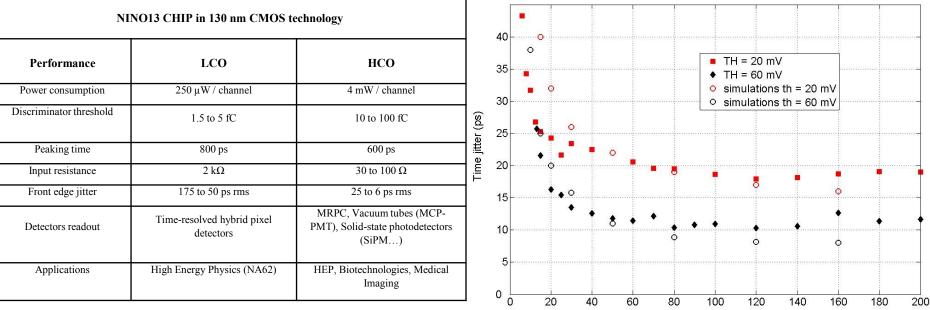


### Power



	Input stage	Feedback	Differential stage	Hysteresis	Stretcher	Driver
Channel Rin = $50 \Omega$	1 mA × 2 <u>2 mA</u>	<u>100 μA</u>	920 μA × 4 <u>3.68 mA</u>	<u>92 µА</u>	<u>Off: 920 µA</u> <u>On: 950 µA</u>	<u>5 mA</u>
Channel Rin = $30 \Omega$	1.8 mA× 2 <u>3.6 mA</u>	<u>100 μA</u>	920 μA × 4 <u>3.68 mA</u>	<u>92 µА</u>	<u>Off: 920 µA</u> <u>On: 950 µA</u>	<u>5 mA</u>
Bias Cell Rin = $30 \Omega$ Rin = $50 \Omega$	N1/N2/N3/P1 <u>2 mA</u> <u>3.6 mA</u>	Ν4/Ρ2 <u>140 μΑ</u> <u>140 μΑ</u>	Ν5 <u>910 μΑ</u> <u>910 μΑ</u>	Ν7 <u>230 μΑ</u> <u>230 μΑ</u>	Ν8 <u>230 μΑ</u> <u>230 μΑ</u>	N6 <u>5 mA</u> <u>5 mA</u>

# NINO 130 nm proto not yet fully optimized



Input charge (fC)